



**100% Material Declaration Data Sheet for
FFV900**

PK776 (v1.0) Jan 22, 2016

FFV900

Average Weight : 11.7917 g

Component	Substance Description	CAS # or Description	% of component	Use in product	Component weight / substance weight (in grams)	Component % of total																								
Silicon die 1	Si	7440-21-3	100.00	basis	0.388303	3.293%																								
					0.388303																									
Bump	Sn Ag	7440-31-5 7440-22-4	98.20 1.80	basis basis	0.015339	0.130%																								
					0.015063 0.000276																									
Underfill	Bisphenol F type liquid epoxy resin 1,6-Bis(2,3-epoxypropoxy)naphthalene Bisphenol A type liquid epoxy resin Amine type hardener Silicon dioxide Carbon black Additives	9003-36-5 27610-48-6	15.00 10.00	basis basis	0.049000	0.416%																								
					0.007350 0.004900																									
		trade secret 60676-86-0 1333-86-4 trade secret	10.00 58.00 1.00 1.00	basis filler color agent additives	0.002450																									
					0.004900																									
					0.028420																									
					0.000490																									
0.000490																														
Solder paste	Sn Ag Cu	7440-31-5 7440-22-4 7440-50-8	96.50 3.00 0.50	metal metal metal	0.005772	0.049%																								
					0.005570 0.000173 0.000029																									
					Capacitor 1		BaTiO3 type Titanium dioxide Misc Ni Cu Silicon dioxide diboron trioxide; boric oxide Ni Sn	1304-28-5 13463-67-7 - 7440-02-0 7440-50-8 7631-86-9 1303-86-2 7440-02-0 7440-31-5	40.00 20.00 6.67 2.42 20.73 1.85 0.45 2.12 5.76	Ceramic Inner electrode Out electrode Plating1 Plating2	0.002400	0.020%																		
											0.000960 0.000480 0.000160 0.000058 0.000498 0.000044 0.000011 0.000051 0.000138																			
Capacitor2	BaTiO3 type Titanium dioxide Misc Ni Cu Silicon dioxide diboron trioxide; boric oxide Ni Sn	1304-28-5 13463-67-7 - 7440-02-0 7440-50-8 7631-86-9 1303-86-2 7440-02-0 7440-31-5	31.67 15.83 5.28 26.67 15.10 1.34 0.33 1.00 2.78	Ceramic Inner Electrode Outer Electrode Plating1 Plating2		0.009200					0.078%																			
						0.002914 0.001456 0.000486 0.002454 0.001389 0.000123 0.000030 0.000092 0.000256																								
						Capacitor3							BaTiO3 type Titanium dioxide Misc Ni Cu Silicon dioxide diboron trioxide; boric oxide Ni Sn	1304-28-5 13463-67-7 - 7440-02-0 7440-50-8 7631-86-9 1303-86-2 7440-02-0 7440-31-5	37.46 18.73 6.24 17.95 15.88 1.41 0.35 0.54 1.44	Ceramic Inner Electrode Outer Electrode Plating1 Plating2	0.021600	0.183%												
																	0.008091 0.004046 0.001348 0.003877 0.003430 0.000305 0.000076 0.000117 0.000311													
																	Capacitor4		BaTiO3 type Titanium dioxide Misc Ni Indium(III) oxide Tin dioxide Frits Nickel Cu Silicon dioxide diboron trioxide; boric oxide Ni Sn	1304-28-5 13463-67-7 - 7440-02-0 1312-43-2 18282-10-5 65997-18-4 7440-02-0 7440-50-8 7631-86-9 1303-86-2 7440-02-0 7440-31-5	37.01 18.51 6.17 4.90 9.15 1.83 5.49 1.83 12.05 0.27 1.07 0.49 1.23	Ceramic Inner Electrode Outer Electrode Plating1 Plating2	0.003800	0.032%						
																							0.001406 0.000703 0.000234 0.000186 0.000348 0.000070 0.000209 0.000070 0.000458 0.000010 0.000041 0.000019 0.000047							
																							Heat sink		Cu Ni	7440-50-8 7440-02-0	98.35 1.65	Main material Main material	7.427400	62.988%
																													7.304848 0.122552	
					Heat sink adhesive		Aluminium Oxide Al2O3 Dimethyl siloxane, dimethylvinyl-terminated	- 68083-19-2	80.00 20.00	Main material Main material		0.120000											1.018%							
												0.096000 0.024000																		
Solder ball	Sn Ag Cu	7440-31-5 7440-22-4 7440-50-8	96.50 3.00 0.50	Main material Main material Main material	0.751829		6.376%																							
					0.725515 0.022555 0.003759																									
					2.997057 2.997057																									
Substrate	Consigned					25.417%																								

Revision History

Date	Version	Description of Revisions
01/22/2016	1	Initial Xilinx release.

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